isc Silicon PNP Power Transistor BDX16

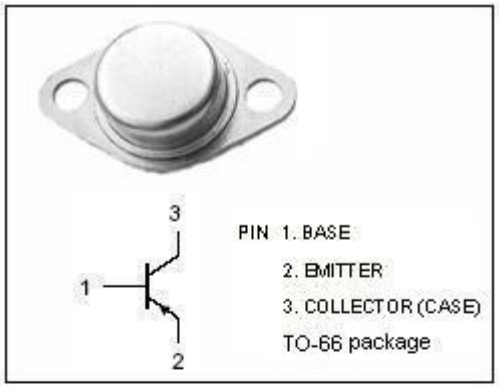
DESCRIPTION

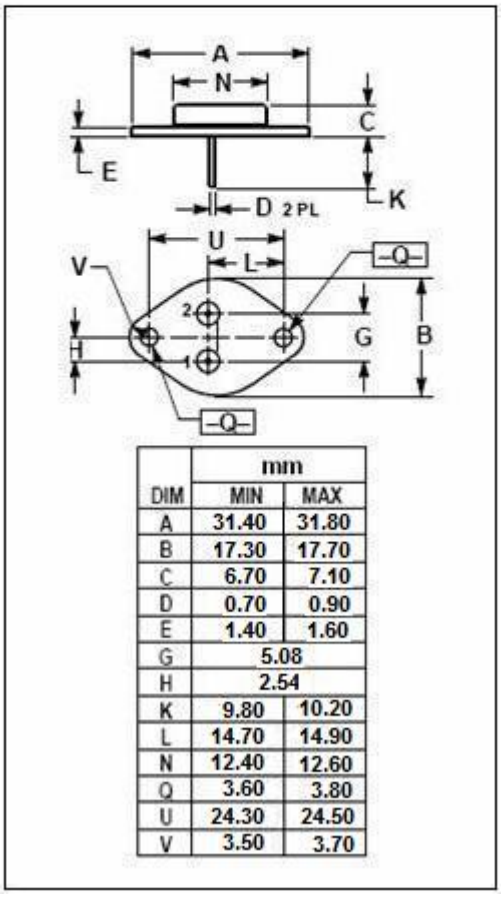
- Contunuous Collector Current-I_C= -3A
- Collector Power Dissipation-
  : P_C= 25W @T_C= 25℃

Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)}$= -140V(Min)

APPLICATIONS

- Designed for use in general purpose switching and linear amplifier applications requiring high breakdown voltages.





DIM	mm MIN	MAX
A	31.40	31.80
B	17.30	17.70
C	6.70	7.10
D	0.70	0.90
E	1.40	1.60
G	5.08	
H	2.54	
K	9.80	10.20
L	14.70	14.90
N	12.40	12.60
Q	3.60	3.80
U	24.30	24.50
V	3.50	3.70

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-160	V
V_{CER}	Collector-Emitter Voltage R_{BE}= 100Ω	-150	V
V_{CEO}	Collector-Emitter Voltage	-140	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-3	A
I_{CM}	Collector Current-Peak	-4	A
I_B	Base Current-Continuous	-2	A
P_C	Collector Power Dissipation@T_C=25℃	25	W
T_J	Junction Temperature	200	℃
T_{stg}	Storage Temperature	-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	7.0	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -100mA; I_B= 0	-140			V
$V_{(BR)CER}$	Collector-Emitter Breakdown Voltage	I_C= -100mA; R_{BE}= 100Ω	-150			V
$V_{(BR)CEX}$	Collector-Emitter Breakdown Voltage	I_C= -100mA; V_{BE}= 1.5V	-160			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -0.5A; I_B= -50mA			-1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -0.5A; V_{CE}= -4V			-1.7	V
I_{CEX}	Collector Cutoff Current	V_{CE}= -140V;V_{BE}= 1.5V V_{CE}= -140V;V_{BE}= 1.5V,T_C=150℃			-1.0 -5.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -7V; I_C= 0			-1.0	mA
h_{FE}	DC Current Gain	I_C= -0.5A; V_{CE}= -4V	20		80	
f_T	Current Gain-Bandwidth Product	I_C= -0.2A; V_{CE}= -10V		4		MHz